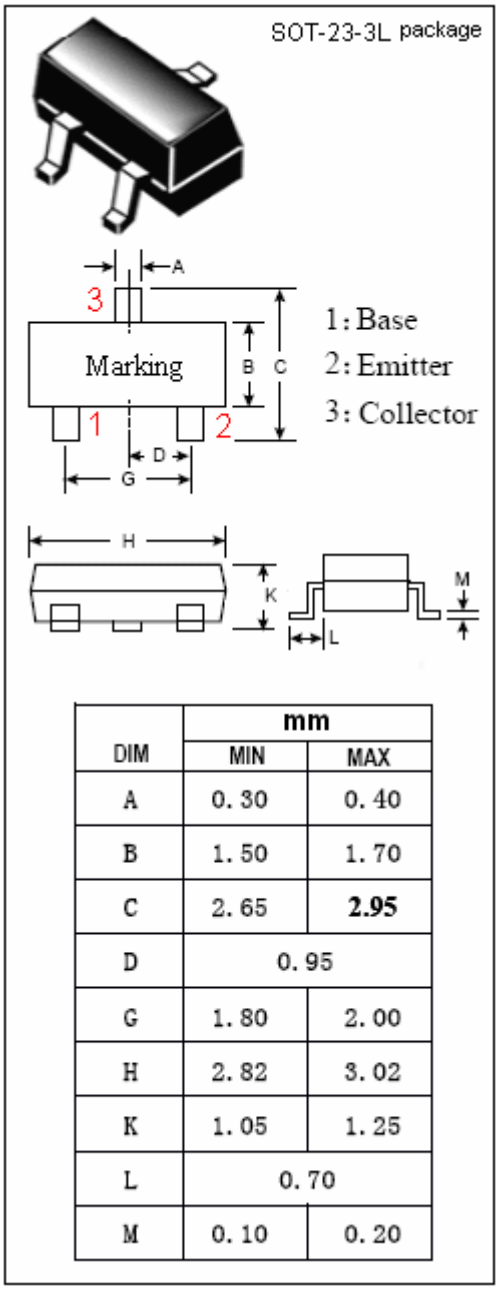
isc Silicon NPN RF Transistor 2SC3125

DESCRIPTION

• Good Linearity of f_T

APPLICATIONS

• Designed for TV Final Picture IF amplifier applications.



DIM	mm MIN	MAX
A	0.30	0.40
B	1.50	1.70
C	2.65	2.95
D	0.95	
G	1.80	2.00
H	2.82	3.02
K	1.05	1.25
L	0.70	
M	0.10	0.20

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current-Continuous	50	mA
I_B	Base Current-Continuous	25	mA
P_C	Collector Power Dissipation @T_C=25℃	0.15	W
T_J	Junction Temperature	125	℃
T_{stg}	Storage Temperature Range	-55~125	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA ; I_B= 0	25			V
I_{CBO}	Collector Cutoff Current	V_{CB}= 30V; I_E= 0			0.1	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 3V; I_C= 0			0.1	μA
h_{FE}	DC Current Gain	I_C= 10mA ; V_{CE}= 10V	20		200	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 15mA ; I_B= 1.5mA			0.2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 15mA ; I_B= 1.5mA			1.5	V
C_{OB}	Output Capacitance	I_E= 0 ; V_{CB}= 10V; f= 1.0MHz		1.1	1.6	pF
$r_{bb'} \cdot C_C$	Base Time Constant	I_C= 1mA ; V_{CB}= 10V; f= 30MHz			25	ps
f_T	Current-Gain—Bandwidth Product	I_C= 10mA ; V_{CE}= 10V	250	600		MHz

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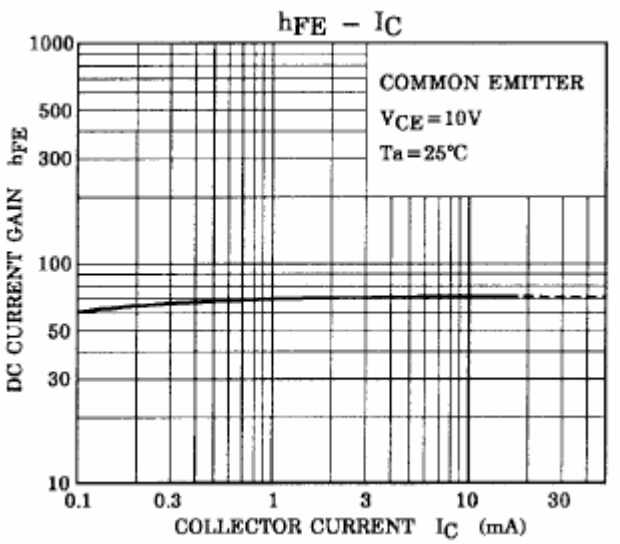

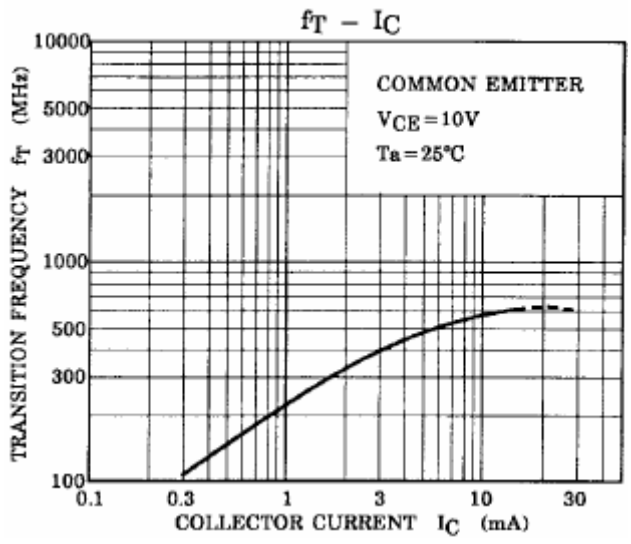

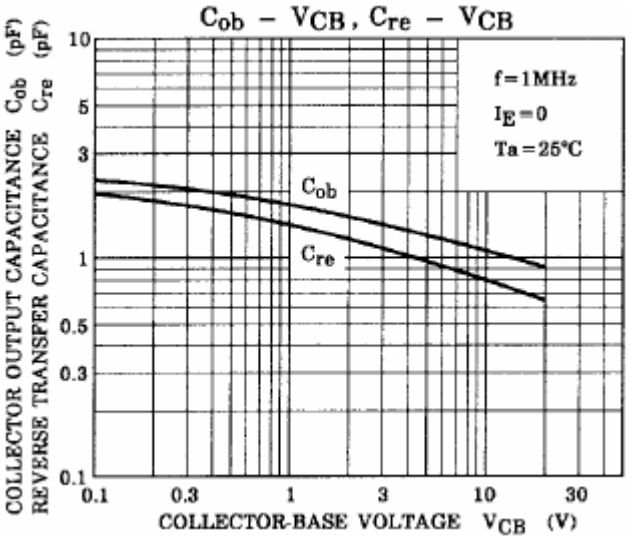

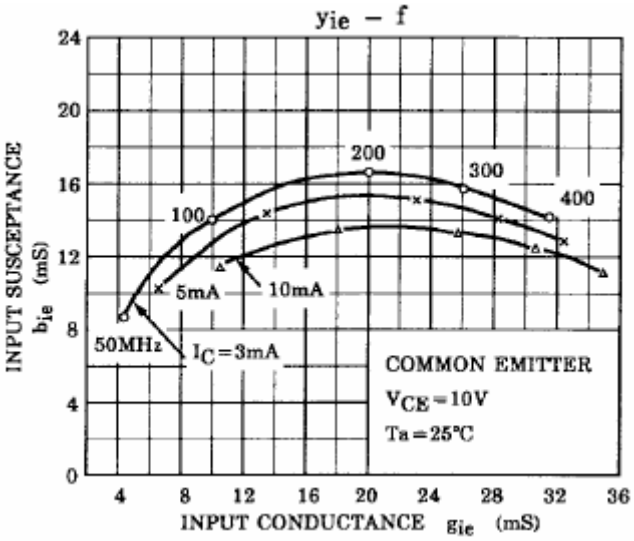

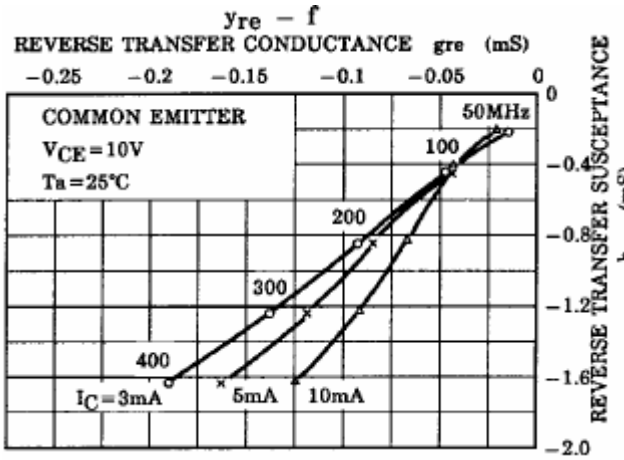

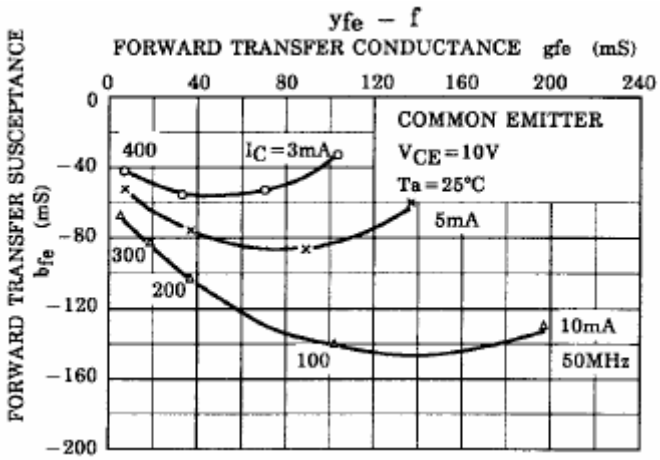

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